

■ PRODUCT CHARACTERISTICS

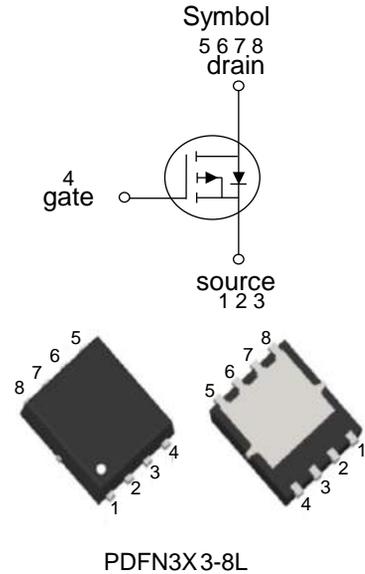
V _{DSS}	-20V
R _{DS(on)} Typ(@V _{GS} =-2.5V)	7.5mΩ
R _{DS(on)} Typ(@V _{GS} =-4.5V)	5.8mΩ
I _D	-45A

■ APPLICATIONS

- PWM applications
- Load switch
- Power management

■ FEATURES

- High power and current handling capability
- Led free product is acquired
- Surface mount package



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-free	Halogen		
N/A	MOT2378J	PDFN3X3-8L	5000pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS(T_C=25°C , unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DSS}	-20	V
Gate-source voltage	V _{GSS}	±10	V
Continuous drain current	I _D	-45	A
Continuous drain current(T _C =100 °C)	I _D	-635	A
Pulsed drain current	I _{DM}	200	A
Single pulsed avalanche energy	E _{AS}	320	mJ
Power dissipation	P _D	80	W
Thermal resistance ,junction to case	R _{θJC}	1.6	°C/W
Junction temperature	T _J	+150	°C
Storage temperature	T _{STG}	-55~ +150	°C

■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-16V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 100	nA
On characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-	-1	V
Drain-Source On-State Resistance	$r_{DS(on)}$	$V_{GS}=-4.5V, I_D=-20A$	-	5.8	7.8	$m\Omega$
		$V_{GS}=-2.5V, I_D=-20A$	-	7.5	11	$m\Omega$
		$V_{GS}=-1.8V, I_D=-20A$	-	9	12	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-20A$	-10	-	-	S
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$	-	7177	-	PF
Output Capacitance	C_{oss}		-	863	-	PF
Reverse Transfer Capacitance	C_{riss}		-	656	-	PF
Switching characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_{GEN}=3\Omega$ $V_{GS}=-4.5V, R_L=0.5\Omega$	-	20	-	nS
Turn-on Rise Time	t_r		-	55	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	100	-	nS
Turn-Off Fall Time	t_f		-	35	-	nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-20A,$ $V_{GS}=-4.5V$	-	63.5	-	nC
Gate-Source Charge	Q_{gs}		-	10	-	nC
Gate-Drain Charge	Q_{gd}		-	18	-	nC
Drain-source diode characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-20A$	-	-	-1.2	V
Diode Forward Current	I_S		-	-	-45	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}, I_F = -20A$	-	70	-	nS
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A/\mu s$	-	60	-	nC

■ TYPICAL CHARACTERISTICS

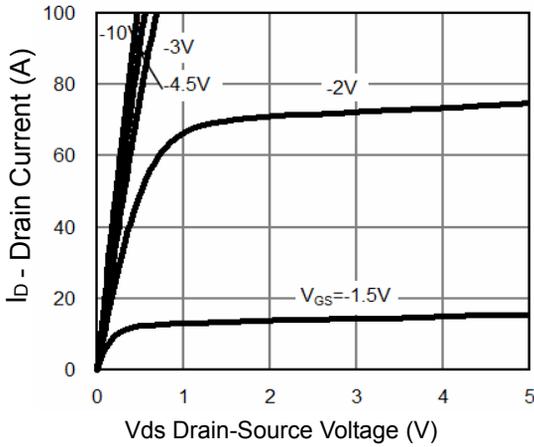


Figure 1 output characteristics

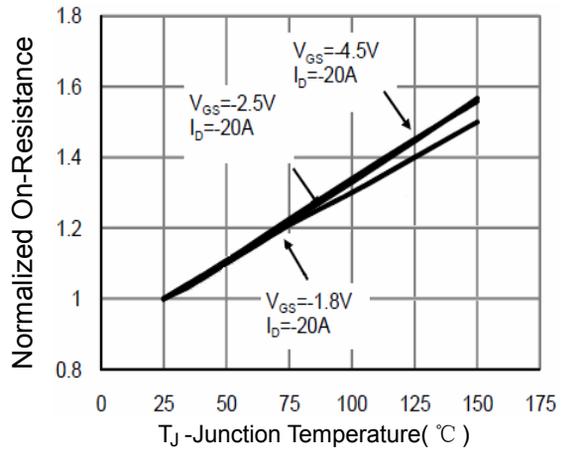


Figure 2 r_{dson} -junction temperature

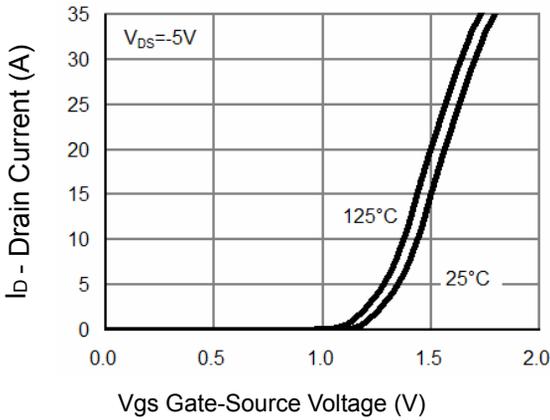


Figure 3 transfer characteristics

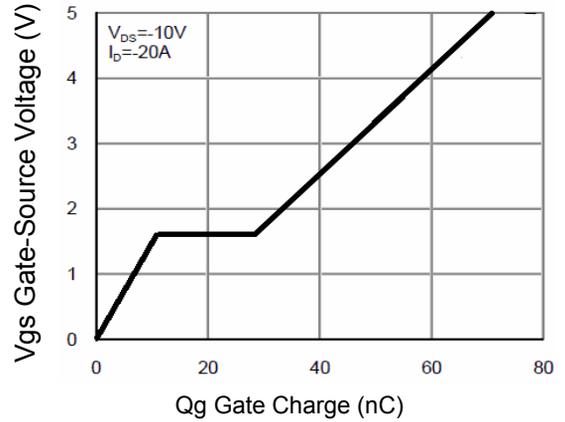


Figure 4 gate charge

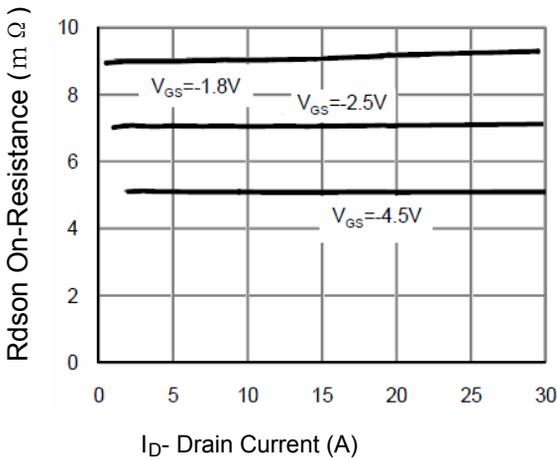


Figure 5 r_{dson} -drain current

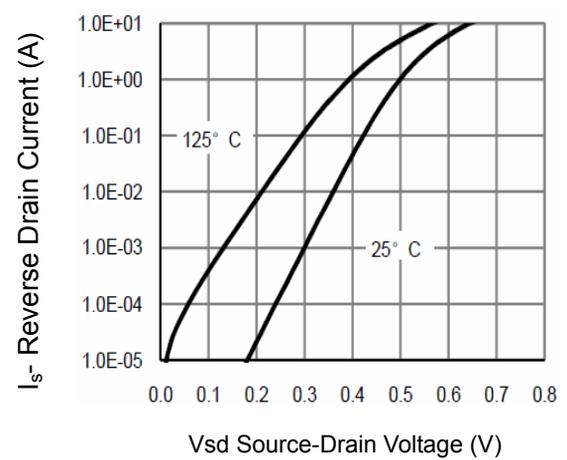


Figure 6 source-drain diode forward

■ TYPICAL CHARACTERISTICS(Cont.)

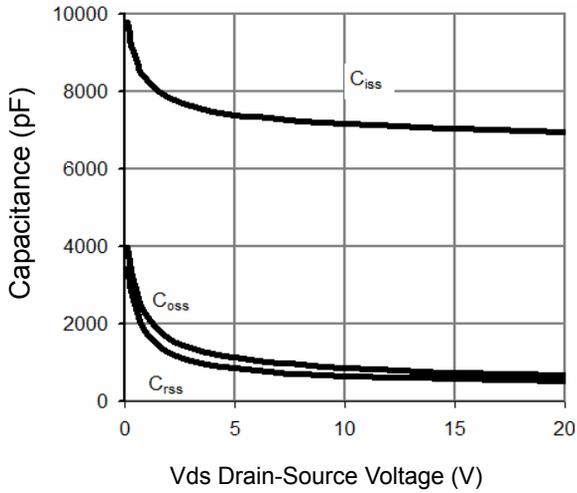


Figure 7 capacitance vs vds

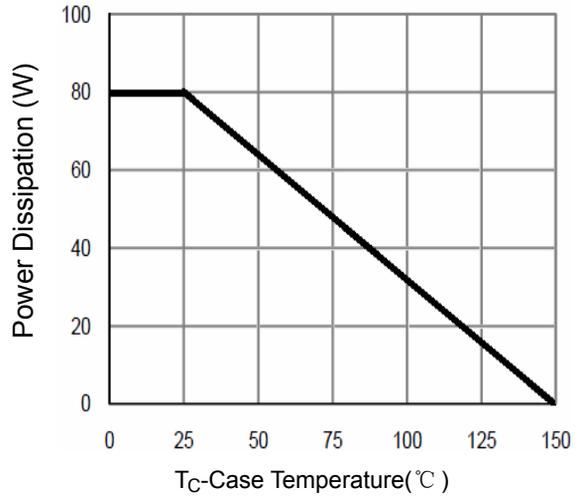


Figure 8 power de-rating

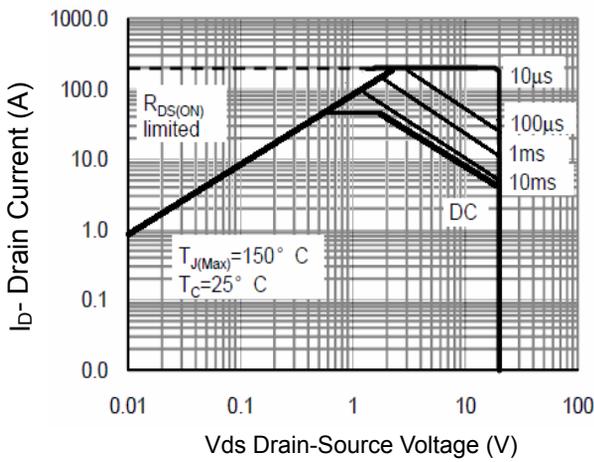


Figure 9 safe operation area

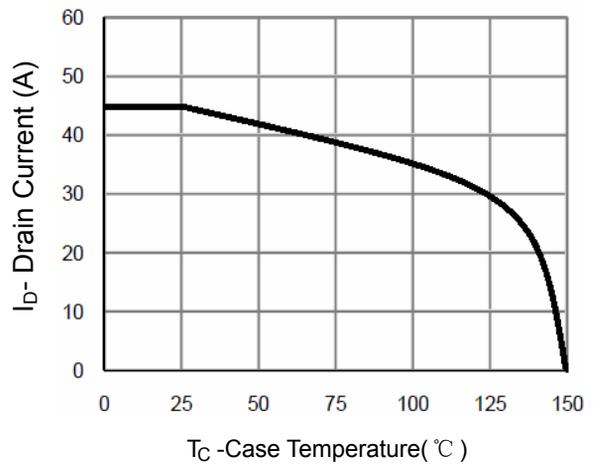


Figure 10 current de-rating

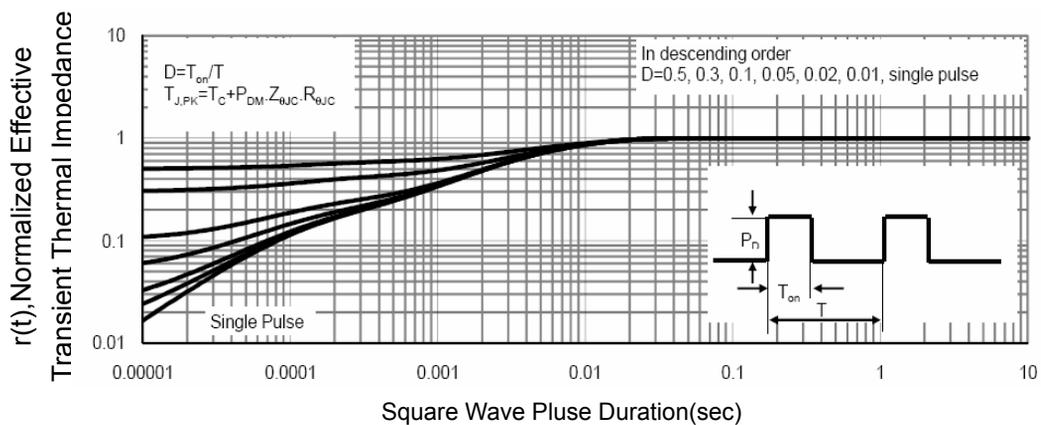
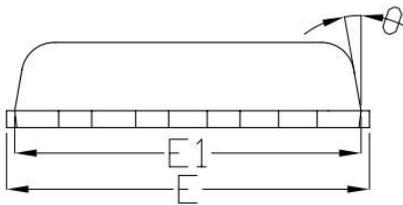
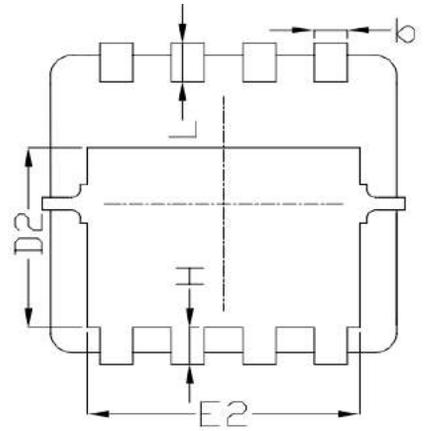
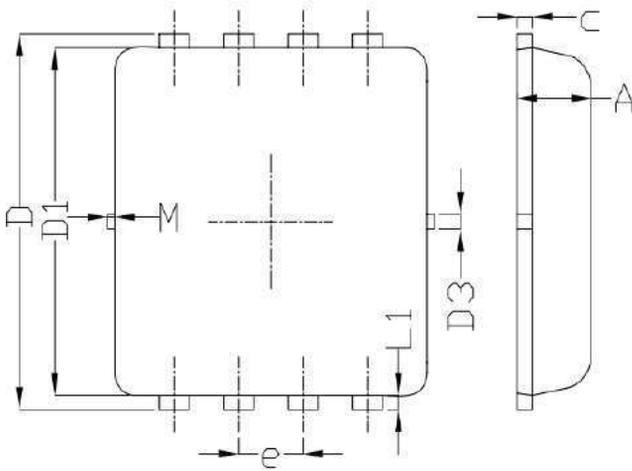
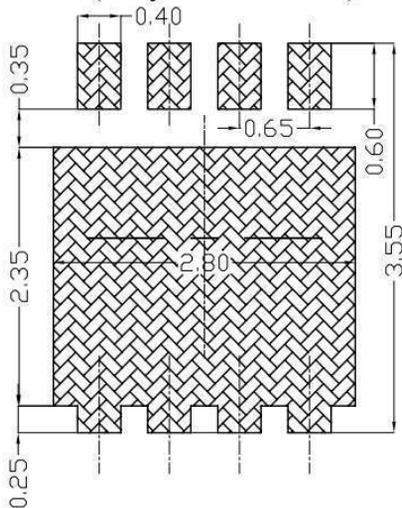


Figure 11 normalized maximum transient thermal impedance

■ PDFN3X3-8L PACKAGE MECHANICAL DATA



Land Pattern
(Only for Reference)



SYMBOL	DIMENSIONAL REQOMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
θ	---	10°	12°
M	*	*	0.15
* Not specified			